

**DESCRIPTION**

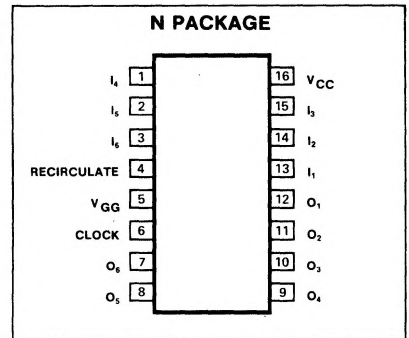
The 2518 32-bit and the 2519 40-bit recirculating static shift registers consist of enhancement mode p-channel silicon gate MOS devices integrated on a single monolithic chip. Internal recirculation logic plus TTL/DTL level clock signals are provided for maximum interfacing ease.

**TRUTH TABLE**

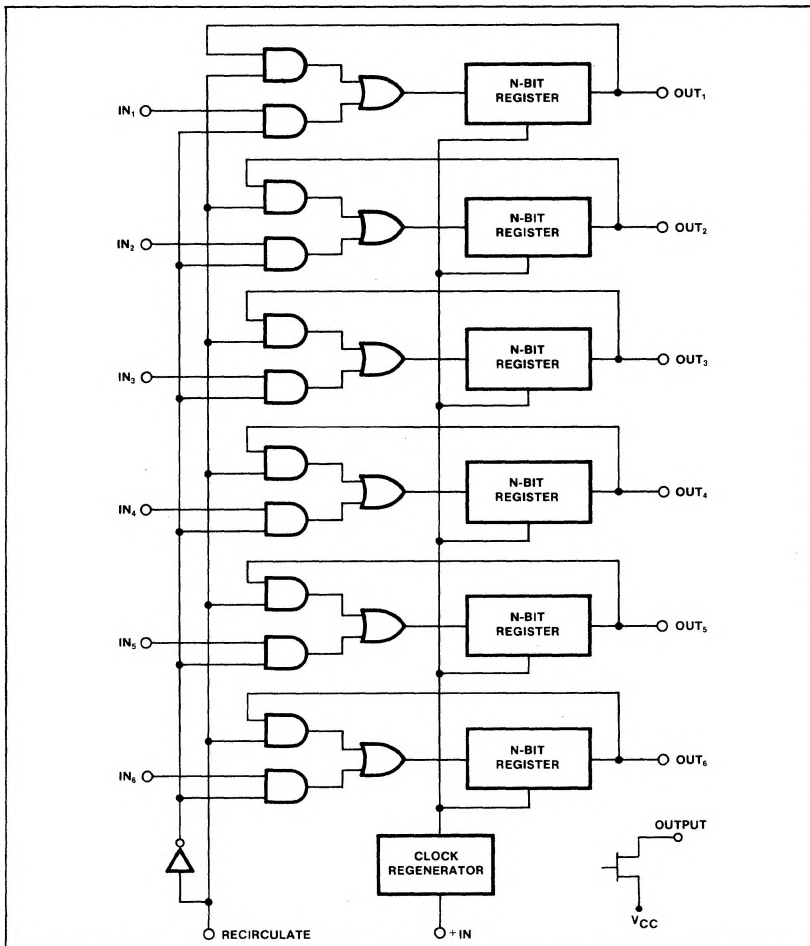
RECIRCULATE	INPUT	FUNCTION
1	0	Recirculate
1	1	Recirculate
0	0	"0" is written
0	1	"1" is written

Data is read out when output enable is low. Output is tristated when output enable is high.

**PIN CONFIGURATION**



**BLOCK DIAGRAM**



**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>**

PARAMETER	RATING	UNIT
$T_A$ Temperature range		$^{\circ}C$
Operating <sup>2</sup>	0 to +70	
$T_{STG}$ Storage	-65 to 150	
$P_D$ Power dissipation at $T_A = 70^{\circ}C$	640	mW
Data and clock input voltages and supply voltages with respect to $V_{CC}$	0.3 to -20	V

**DC ELECTRICAL CHARACTERISTICS**  $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = +5\text{V} \pm 5\%$ ,  $V_{GG} = -12\text{V} \pm 5\%$   
 unless otherwise specified.<sup>3,4,5,6,7</sup>

PARAMETER	TEST CONDITIONS	LIMITS			UNIT	
		Min	Typ	Max		
$V_{IL}$	Input voltage <sup>8</sup> Low			0.6	V	
$V_{IH}$	High	3.4		5.3		
$V_{ILC}$	Clock low			0.6		
$V_{IHC}$	Clock high	3.4		5.3		
$V_{OL}$	Output voltage Low					
$V_{OH}$	High	$I_{OL} = 1.6\text{mA}$ $I_{OH} = 100\mu\text{A}$	3.8	0.5	V	
$I_{LO}$	Leakage current Output	$T_A = 25^\circ\text{C}$		10	nA	
$I_{LC}$	Clock	$V_{ILC} = \text{GND}$		1000		
$I_{LI}$	Input load current	$V_{IN} = -5.5\text{V}$ , $T_A = 25^\circ\text{C}$		10	nA	
$I_{GG}$	Supply current	Continuous operation, $T_A = 25^\circ\text{C}$ , $f = 1.5\text{MHz}$		16	25	mA
$C_{IN}$	Capacitance Input	At 1MHz, $V_{AC} = 25\text{mV p-p}$ $V_{IN} = V_{CC}$		5	7	pF
$C_\phi$	Clock	$V_\phi = V_{CC}$		6	7	

**AC ELECTRICAL CHARACTERISTICS**  $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = +5\text{V} \pm 5\%$ ,  $V_{GG} = -12\text{V} \pm 5\%$ ,  $V_{ILC} = 0.4\text{V}$  to  $4.0\text{V}$

PARAMETER	TO	FROM	LIMITS			UNIT	
			Min	Typ	Max		
Freq.	Clock rep rate		dc	3	2	MHz	
$t_{\phi PW}$	Pulse width Clock <sup>10</sup>		.300		100	$\mu\text{s}$	
$t_{\phi W}$	Clock		.200		dc		
$t_{DS}$	Setup and hold time Setup time	Clock in	Data in	100		ns	
$t_{DH}$	Hold time	Data in	Clock in	70			
$t_{RS}$	Setup time	Clock	Recirculate	150			
$t_{RH}$	Hold time	Recirculate	Clock	50			
$t_{R,TF}$	Clock pulse transition				5	$\mu\text{s}$	
$t_A$	Clock to data out delay	Data	Clock		300	350	ns

**NOTES**

- Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any of this specification is not implied.
- For operating at elevated temperatures the device must be derated based on a  $150^\circ\text{C}$  maximum junction temperature and a thermal resistance of  $125^\circ\text{C C/W}$ , junction to ambient.
- All inputs are protected against static charge.
- Parameters are valid over operating temperature range unless specified.
- All voltage measurements are referenced to ground.
- Manufacturer reserves the right to make design and process changes and improvements.
- Typical values are at  $+25^\circ\text{C}$  and typical supply voltages.
- Guaranteed input levels are stated for worst case conditions including a  $\pm 5\%$  variation in  $V_{CC}$  and a temperature variation of  $0^\circ\text{C}$  to  $+70^\circ\text{C}$ . Actual input requirements with respect to  $V_{CC}$  are  $V_{IH} = V_{CC} - 1.85\text{V}$  and  $V_{IL} = V_{CC} - 4.15\text{V}$ .
- $V_{OL}$  is dependent on  $R_L$  and input characteristics of driven gate.
- Input rise and fall times = 10ns. Output load is 1 TTL gate.
- For static operation, clock must be stopped in TTL high state in order to retain data (see clock pulse width specification).

**TIMING DIAGRAM**

